

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. -5. (Canceled)

6. (Previously Presented) An electroluminescence display device comprising:
a substrate having an insulating surface;

a first thin film transistor disposed over said substrate, wherein said first thin film transistor comprises an active layer comprising crystalline silicon including source, drain and channel regions, and a gate electrode adjacent to the channel region;

a second thin film transistor disposed over said substrate, said second thin film transistor comprising an active layer comprising crystalline silicon including source, drain and channel regions, and a gate electrode adjacent to the channel region, said gate electrode of the second thin film transistor being electrically connected to said drain region of the first thin film transistor;

an electrode comprising aluminum for electrically connecting said transparent electrode and said drain region of the second thin film transistor; and

an electroluminescence layer comprising an organic material disposed adjacent to said transparent electrode,

wherein a direct contact between said electrode and said transparent electrode and a direct contact between said electrode and said drain region of the second thin film transistor are prevented by a barrier metal layer comprising titanium interposed therebetween.

7. (Previously Presented) An electroluminescence display device according to claim 6 wherein said barrier metal layer further contains nitrogen.

8. (Previously Presented) An electroluminescence display device according to claim 6 further comprising a counter electrode opposed to said transparent electrode with said organic electroluminescence layer interposed therebetween, wherein said counter electrode comprises magnesium and silver.

9.-11. (Canceled)

12. (Currently Amended) An electroluminescence display device comprising:
a substrate having an insulating surface;
a thin film transistor formed over said substrate, said thin film transistor comprising an active layer comprising crystalline silicon including source, drain and channel regions;
an electrode comprising aluminum electrically connected to one of said source and drain regions;
a barrier metal layer interposed between said electrode and said one of the source and drain regions to prevent a direct contact therebetween;
a transparent electrode electrically connected to said thin film transistor; and
an electroluminescence layer comprising an organic material adjacent to said transparent electrode,
wherein said barrier metal layer comprises titanium,
~~The display device according to claim 1 wherein said barrier metal layer comprises titanium nitride where a concentration of nitrogen is less than 50 atm%.~~

13. (Previously Presented) The display device according to claim 6 wherein said conductive layer comprises titanium nitride where a concentration of nitrogen is 50 atm% or less.

14. (Currently Amended) An electroluminescence display device comprising:
a substrate having an insulating surface;
a thin film transistor formed over said substrate, said thin film transistor
comprising an active layer comprising crystalline silicon including source, drain and
channel regions;
an electrode comprising aluminum electrically connected to one of said source
and drain regions;
a barrier metal layer interposed between said electrode and said one of the
source and drain regions to prevent a direct contact therebetween;
a transparent electrode electrically connected to said thin film transistor;
an electroluminescence layer comprising an organic material disposed adjacent
to said transparent electrode, and
a peripheral driving circuit comprising another thin film transistor formed over
said substrate.

~~The display device according to claim 9 wherein said conductive layer barrier~~
~~metal layer comprises titanium nitride where a concentration of nitrogen is less than 50~~
~~atm%.~~

15.-19. (Canceled)

20. (Previously Presented) The display device according to claim 12 wherein
said concentration of nitrogen is not higher than 15 atm%.

21. (Currently Amended) The display device according to claim [[9]] 14 wherein
said conductive layer comprises titanium nitride where a concentration of nitrogen is not
higher than 15 atm%.

22. (New) An electroluminescence display device according to claim 12 wherein said transparent electrode comprises indium tin oxide.